

Pressure dependence of shallow bound states in gallium

Solid State Communications

53, 1069-1076

DOI: [10.1016/0038-1098\(85\)90882-8](https://doi.org/10.1016/0038-1098(85)90882-8)

Citation Report

#	ARTICLE	IF	CITATIONS
1	The use of hydrostatic pressure and alloying to introduce deep levels in the forbidden gap of InSb, GaAs, and Ga $_{1-x}$ Al $_x$ As. , 1985, , 591-603.		5
2	Zone folding, morphogenesis of charge densities, and the role of periodicity in GaAs-Al $_x$ Ga $_{1-x}$ As (001) superlattices. Physical Review B, 1986, 34, 2416-2427.	3.2	109
3	High pressure dependence of the electronic properties of bound states in n-type GaAs. Solid State Communications, 1986, 58, 289-293.	1.9	38
4	Magneto-optical studies of n-GaAs under high hydrostatic pressure. Semiconductor Science and Technology, 1986, 1, 264-274.	2.0	63
5	High-pressure study of photoluminescence in indium phosphide at low temperature. Physical Review B, 1986, 33, 5896-5898.	3.2	43
6	Band-structure determination of GaAs from hot-electron luminescence. Physical Review B, 1986, 33, 2953-2956.	3.2	57
7	Hall effect measurement in the diamond anvil high-pressure cell. Review of Scientific Instruments, 1986, 57, 2795-2797.	1.3	30
8	Model calculation of nitrogen properties in III-IV compounds. Physical Review B, 1986, 33, 2701-2712.	3.2	35
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11	Time decays of donor-bound excitons in GaAs under pressure-induced Γ -X crossover. Physical Review B, 1986, 33, 8373-8378.	3.2	22
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